

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3267

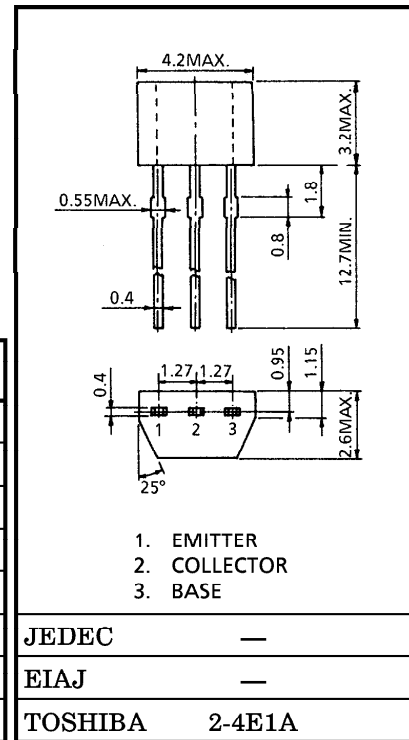
POWER AMPLIFIER APPLICATIONS
POWER SWITCHING APPLICATIONS

Unit in mm

- Low Saturation Voltage : $V_{CE(sat)} = 0.5V (Max.) @ I_C = 2A$
- Complementary to 2SA1297

MAXIMUM RATINGS ($T_a = 25^\circ C$)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|-----------------------------|-----------|---------|------------|
| Collector-Base Voltage | V_{CBO} | 20 | V |
| Collector-Emitter Voltage | V_{CEO} | 20 | V |
| Emitter-Base Voltage | V_{EBO} | 6 | V |
| Collector Current | I_C | 2 | A |
| Base Current | I_B | 0.5 | A |
| Collector Power Dissipation | P_C | 400 | mW |
| Junction Temperature | T_j | 150 | $^\circ C$ |
| Storage Temperature Range | T_{stg} | -55~150 | $^\circ C$ |



Weight : 0.13g

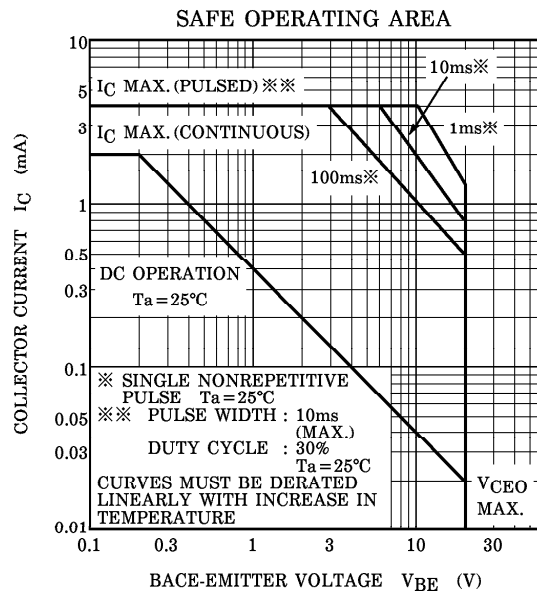
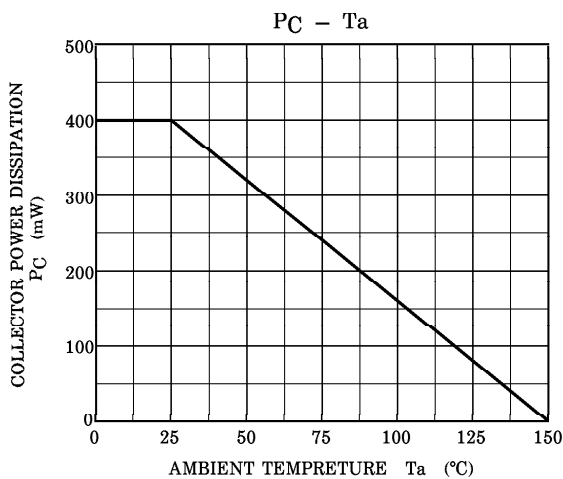
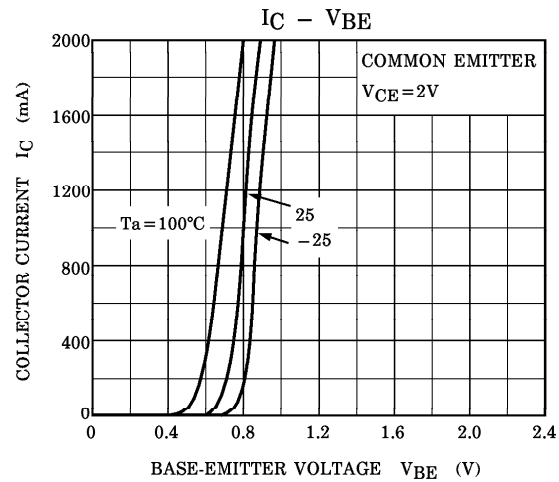
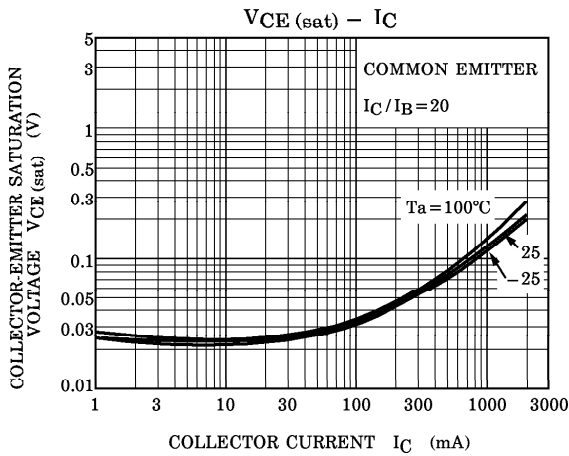
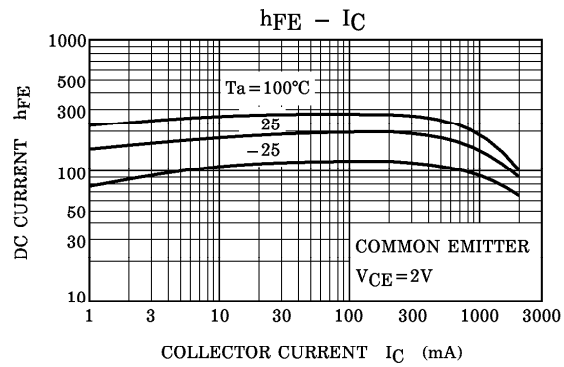
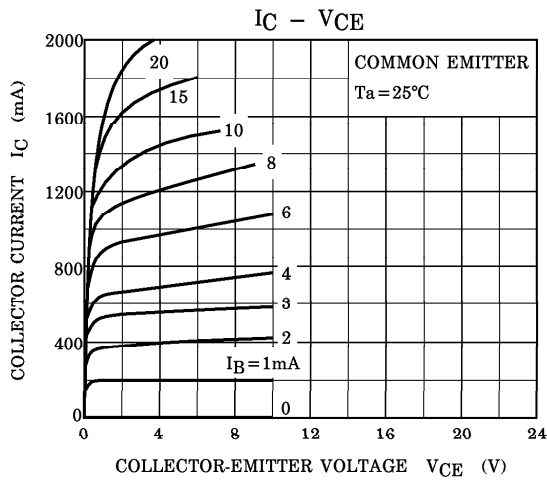
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|--------------------|-----------------------------------|------|------|------|---------|
| Collector Cut-off Current | I_{CBO} | $V_{CB} = 20V, I_E = 0$ | — | — | 0.1 | μA |
| Emitter Cut-off Current | I_{EBO} | $V_{EB} = 6V, I_C = 0$ | — | — | 0.1 | μA |
| Collector-Emitter Breakdown Voltage | $V_{(BR) CEO}$ | $I_C = 10mA, I_B = 0$ | 20 | — | — | V |
| Emitter-Base Breakdown Voltage | $V_{(BR) EBO}$ | $I_E = 0.1mA, I_C = 0$ | 6 | — | — | V |
| DC Current Gain | $h_{FE(1)}$ (Note) | $V_{CE} = 2V, I_C = 100mA$ | 120 | — | 700 | |
| | $h_{FE(2)}$ | $V_{CE} = 2V, I_C = 2A$ | 75 | — | — | |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 2A, I_B = 0.1A$ | — | — | 0.5 | V |
| Base-Emitter Voltage | V_{BE} | $V_{CE} = 2V, I_C = 0.1A$ | — | — | 0.85 | V |
| Transition Frequency | f_T | $V_{CE} = 2V, I_C = 0.5A$ | — | 120 | — | MHz |
| Collector Output Capacitance | C_{ob} | $V_{CB} = 10V, I_E = 0, f = 1MHz$ | — | 30 | — | pF |

Note : $h_{FE(1)}$ Classification Y : 120~240, GR : 200~400, BL : 350~700

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